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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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### MS2422

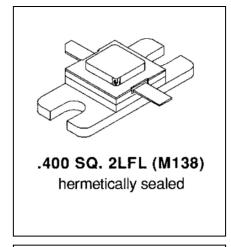
# RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

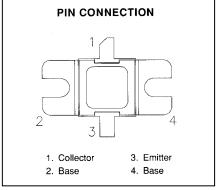
#### Features

- DESIGNED FOR HIGH POWER PULSED IFF, DME, AND TACAN APPLICATIONS
- 350 W (typ.) IFF 1030 1090 MHz
- 300 W (min.) DME 1025 1150 MHz
- 290 W (typ.) TACAN 960 1215 MHz
- 960 1215 MHz
- GOLD METALLIZATION
- P<sub>OUT</sub> = 300W MINIMUM
- $G_P = 6.3 \text{ dB MINIMUM}$
- INFINITE VSWR CAPABILITY @ RATED CONDITIONS
- EMITTER BALLASTED
- COMMON BASE

### **DESCRIPTION:**

The MS2422 is a gold metallized silicon, NPN power transistor designed for applications requiring high peak power and low duty cycles such as IFF, DME, and TACAN. The MS2422 is designed with internal input/output matching resulting in improved broadband performance and low thermal resistance.





### ABSOLUTEMAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	65	V
V <sub>CES</sub>	Collector-Emitter Voltage	65	V
V <sub>EBO</sub>	Emitter-Base Voltage	3.5	V
Ic	Device Current	22	Α
P <sub>DISS</sub>	Power Dissipation	875	W
T <sub>J</sub>	Junction Temperature	200	ōC
T <sub>STG</sub>	Storage Temperature	-65 to +150	ōC

#### Thermal Data

R <sub>TH(J-C)</sub> Junction-case Thermal Resistance	0.20	°C/W
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# MS2422

# ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

### **STATIC**

Symbol	Test Conditions		Value			
		Min.	Тур.	Max.	Unit	
BV <sub>CBO</sub>	I <sub>C</sub> = 10 mA	I <sub>E</sub> = 0 mA	65			V
BV <sub>CES</sub>	I <sub>C</sub> = 25 mA	$V_{BE} = 0 V$	65			V
BV <sub>EBO</sub>	I <sub>E</sub> = 5.0 mA	$I_C = 0 \text{ mA}$	3.5			V
I <sub>CES</sub>	V <sub>CE</sub> = 50 V	I <sub>E</sub> = 0 mA			25	mA
h <sub>FE</sub>	V <sub>CE</sub> = 5 V	I <sub>C</sub> = 1A	10			mA

#### **DYNAMIC**

Symbol	Test Conditions		Value		Unit	
Syllibol			Min.	Тур.	Max.	Unit
P <sub>OUT</sub>	f = 1025 - 1150 MHz P <sub>IN</sub> = 70W	V <sub>CE</sub> = 50V	300			W
G <sub>P</sub>	f = 1025 - 1150 MHz P <sub>IN</sub> = 70W	V <sub>CE</sub> = 50V	6.3			dB
ης	f = 1025 - 1150 MHz P <sub>IN</sub> = 70W	V <sub>CE</sub> = 50V	35			%
Conditions	Pulse Width = 10 μs Duty Cycle = 1%					

### **IMPEDANCE DATA**

FREQ $Z_{IN}(\Omega)$		$Z_{\mathtt{CL}}(\Omega)$
960 MHz	5.1 + j1.0	2.2 – j3.5
1090 MHz	4.2 + j0.5	2.5 – j3.5
1215 MHz	7.5 + j1.5	2.3 – j1.5

Pin = 70W Vce = 50V



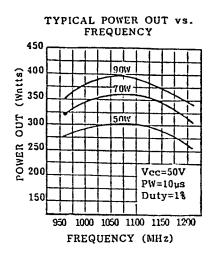
# MS2422

### TYPICAL PERFORMANCE

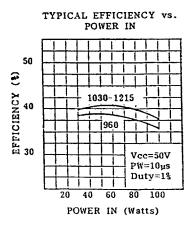
#### POWER OUTPUT vs POWER INPUT

#### TYPICAL POWER OUT vs. POWER IN 450 400 POWER OUT (Watts) 350 300 1030 250 1090 1150 Vcc=50V 200 1200 PW=10us 1215 Duty=1% 150 20 40 60 80 100 POWER IN (Watts)

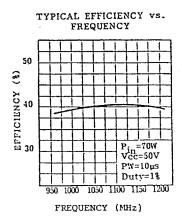
#### POWER OUTPUT vs FREQUENCY



#### **EFFICIENCY vs POWER INPUT**



#### **EFFICIENCY vs FREQUENCY**



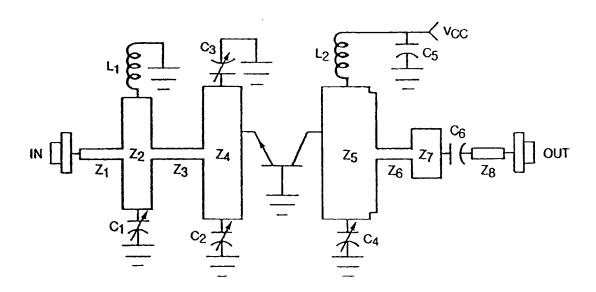




### **TEST CIRCUIT**

Teflon Fiberglass  $\mathcal{E}_{\Gamma} = 2.5$  THK .031





#### All Dimension are in Inches

C1,C2.		71	: .404 x .075
-	.6 - 4.5pF JOHANSON Gigatrim		: .263 x .995
	1000μF, 63V, Electrolytic		: .483 x .077
C6 :	100pF Chip Capacitor Across .090 Gap	<b>Z</b> 4	: .350 x 1.203
		75	

L1 : 2 Turns #24 .12 I.D., Spaced Wire Diameter
L2 : 4 Turns #24, .07 I.D., Spaced Wire Diameter
L2 : 3.335 x .076

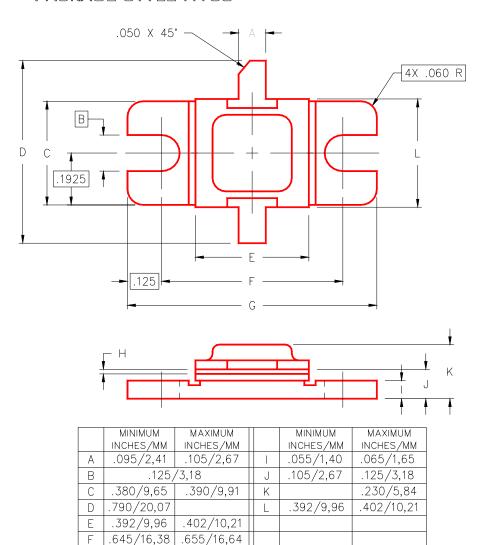
Z6 : .335 x .076 Z7 : .260 x .442 Z8 : .310 x .082



# MS2422

### PACKAGE MECHANICAL DATA

#### PACKAGE STYLE M138



.905/22,99

G

.895/22,73

.002/0,05